

POWER FACTOR CONTROLLER

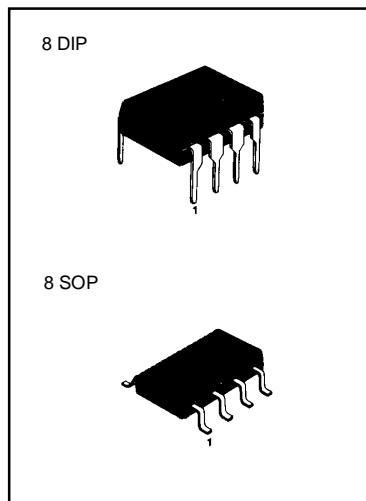
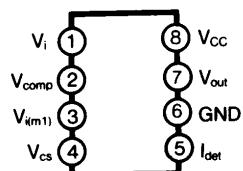
The KA7524B provides the necessary features to implement the Electronic BALLAST control and S.M.P.S application for designing on active power factor correction circuit.

FEATURES

- Internal self-starting
- Micro power start up mode
- Included under voltage lockout circuit
- Internal 1% reference
- High output current : Peak 500mA

CONNECTION DIAGRAM

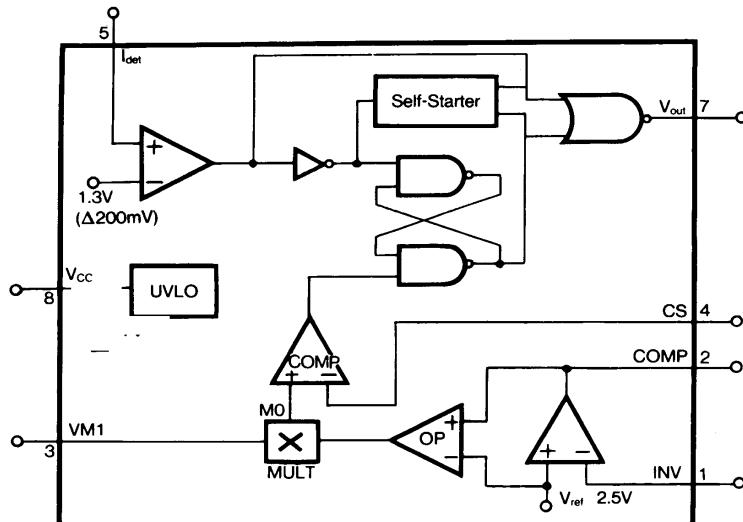
KA7524/KA7524D (8 DIP, 8 SOP)



ORDERING INFORMATION

Device	Ref. Voltage	Package	Operating Temperature
KA7524B	1%	8 DIP	-25 ~ + 100 °C
KA7524BD	1%	8 SOP	

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Value	Unit
Supply Voltage	V_{CC}	20	V
Peak driver output current	$I_{O(P)}$	500	mA
Detect clamping diode current	I_{DET}	10	mA
Output clamping diode current	$I_{O(C,D)}$	10	mA
Operating ambient temperature	T_{OPR}	-25 ~ + 100	°C
Storage Temperature	T_{STG}	-65 ~ + 150	°C

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Under Voltage Lockout Section						
Start Threshold Voltage	$V_{TH(ST)}$		9.2	10	10.8	V
UV Lockout Hysteresis	V_{THS}		1.8	2.0	2.2	V
Supply Current Section						
Start-Up Supply Current	I_{START}	$V_{CC} < V_{TH}$		0.25	0.5	mA
Operating Supply Current	I_{CC}	$V_{CC} = 12V$, No Load		6	12	mA
Dynamic Operating Current	$I_{CC(D)}$	$V_{CC} = 12V$, $f = 50KHz$, $C_{GS} = 1000PF$		10	20	mA
Reference Section(Note1)						
Reference Voltage	V_{REF}	KA7524B/BD	2.475	2.5	2.525	V
Line regulation	V_{REF}	$12V < V_{CC} < 16V$		0.1	10	mV
Load Regulation	V_{REF}	$0 < I_{REF} < 2mA$		0.1	10	mV
Temperature Stability	ST_T			20		mV
Error Amplifier Section						
Input Offset Voltage	V_{IO}		-15		15	mV
Input Bias Current	I_{BIAS}		-1	-0.1	1	uA
Large Signal Open Loop Gain	G_V		60	100		dB
Power Supply Rejection Ratio	$PSRR$		60	86		dB
Output Current	I_{SOURCE}		2			mA
	I_{SINK}				-2	mA
Output Voltage Range	$V_{O(P)}$		1.2		4	V
Unity Gain Bandwidth	UBW			1.0		MHz
Phase Margin	MPH			57		°C



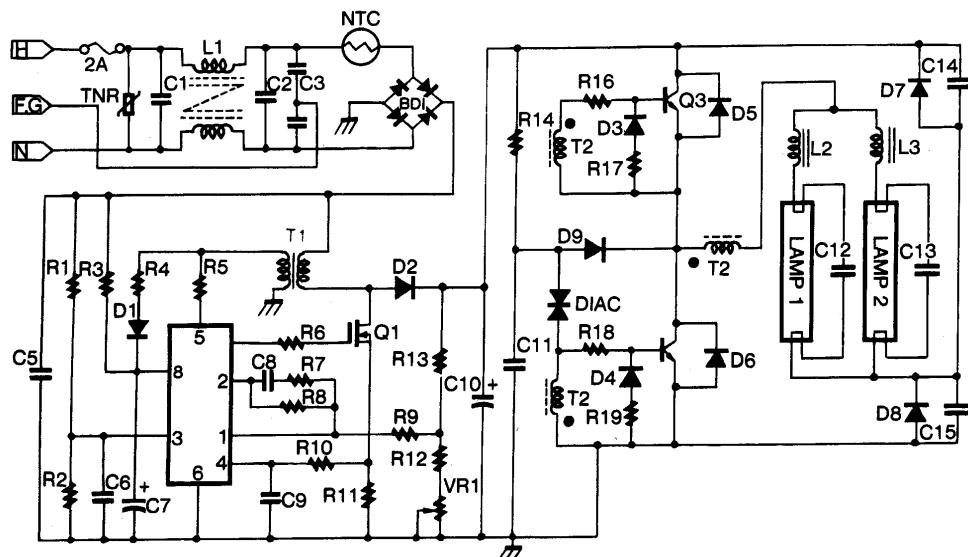
ELECTRICAL CHARACTERISTICS(Continued)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Multiplier Section						
M1 Input Voltage Range	$V_{I(M1)}$		0		2	V
M2 Input Voltage Range	$V_{I(M2)}$		V_{REF}		V_{REF+1}	V
Input Bias Current	I_{BIAS}		-2	-0.5	2	uA
Multiplier Gain (Note2)	G_V	$V_{I(M1)} = 0.5V, V_{I(M2)} = 3V$		0.8		uA
Multiplier Gain Stability	ST_T			-0.2		%/°C
Current Sense Section						
Input Offset Voltage	V_{IO}		-10		10	mV
Input Bias Current	I_{BIAS}	$0V < V_{CS} < 1.7V$	-5		5	uA
C. Sense Delay to Output	$t_{D(S)}$	Error Amp Output = 3.7V		200	500	nS
Current Detect Section						
Input Voltage Threshold	V_{TH}		1.0	1.3	1.6	V
Hysteresis	V_{THS}			200		mV
Input Low Clamp Voltage	$V_{IC(L)}$	$I_{DET} = 0mA$			0.95	V
Input High Clamp Voltage	$V_{IC(H)}$	$I_{DET} = 3mA$	6.1	7.1		V
Input Current	I_J	$0.9 < V_{DET} < 6V$		5		uA
Input Clam Diode Current	I_{CD}	$V_{DET} < 0.9V, V_{DET} > 6V$			3	mA
Self-Starting Section						
Self-Starting Time	t_{SS}		12			uS

Note 1. Reference can not be tested on the PKG

2. $G_V = V_{O(H)} / (V_{I(M1)} * V_{I(M2)} - V_{REF})$ 

KA7524B/BD APPLICATION CIRCUIT

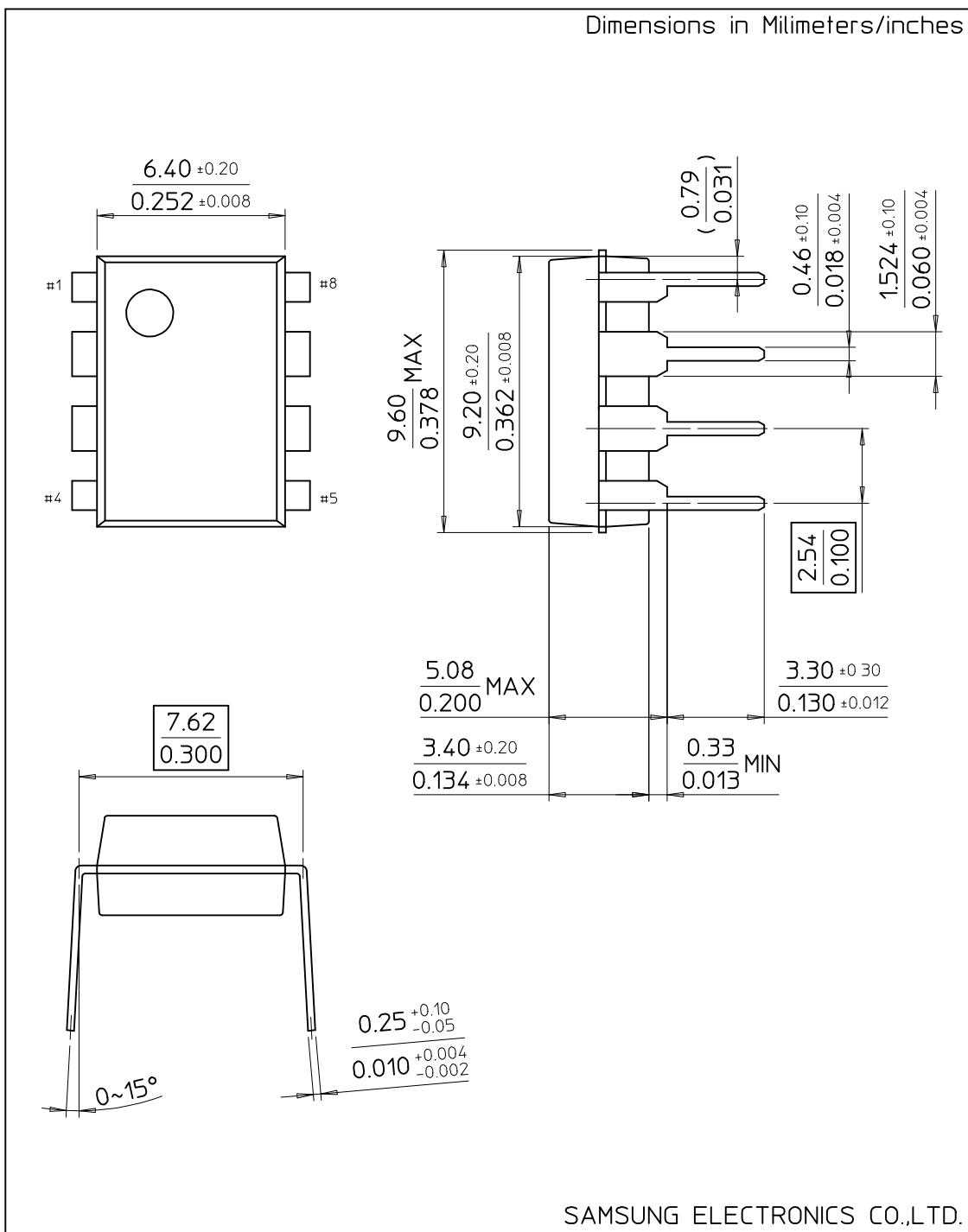


PART LIST

Resistor	Capacitor	Semiconductor
R1 1.8M	C1 0.1uF	IC1 KA7524B
R2 10K	C2 0.1uF	Q1 IRF830
R3 100K	C3 4700pF	Q2 KSC5039
R4 3.3ohm	C4 4700pF	Q3 KSC5039
R5 22K	C5 0.1uF	D1 1N4004
R6 27ohm	C6 0.01uF	D2 1N4937
R7 2.2K	C7 100uF	D3 1N4148
R8 2.2M	C8 0.1uF	D4 1N4148
R9 150K	C9 3300pF	D5 FR107
R10 330ohm	C10 47uF/450V	D6 FR107
R11 0.75ohm	C11 0.1uF	D7 FR107
R12 5.1K	C12 3300pF	D8 FR107
R13 1M	C13 3300pF	BD1 PBP204
R14 390K	C14 0.01uF	TNR 12G471
R15 3.9M	C15 0.01uF	DIAIC 32V
R16 5.1ohm		
R17 27ohm		
R18 5.1ohm	Magnetics	
R19 27ohm	T1 EI-25 (PC30): P = 70T, S = 4T, Gap = 0.5mm	
VR1 5K	T2 D15 (GP-5): P = 3T, S = 13T	
NTC 10ohm	L1 EE-25 (Iron Power) 80mH	
	L2, L3 EI-25 (PC30): 150T, Gap = 0.4mm	

8-DIP-300

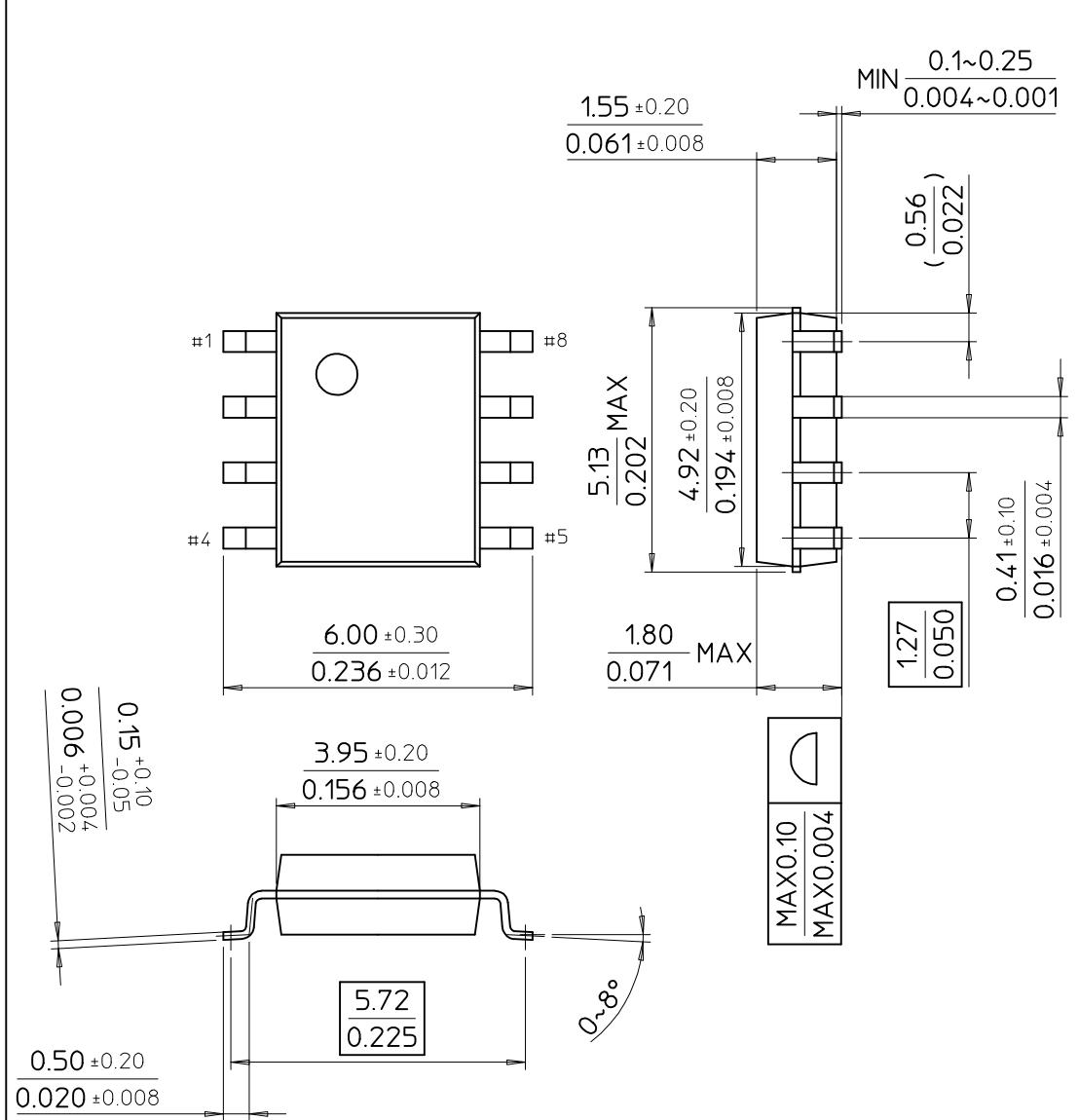
Dimensions in Millimeters/inches



SAMSUNG ELECTRONICS CO.,LTD.

8-SOP-225

Dimensions in Millimeters/inches



SAMSUNG ELECTRONICS CO.,LTD.